

MBR2H100SFT3G

Surface Mount Schottky Power Rectifier

Plastic SOD-123FL Package

This device uses the Schottky Barrier principle with a large area metal-to-silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC-DC and DC-DC converters, reverse battery protection, and “Oring” of multiple supply voltages and any other application where performance and size are critical.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0
- Package Designed for Optimal Automated Board Assembly
- ESD Ratings: Machine Model, C
Human Body Model, 3B
- This is a Pb-Free Device

Mechanical Characteristics

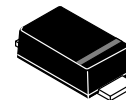
- Reel Options: MBR2H100SFT3G = 10,000 per 13 in reel/8 mm tape
- Device Marking: L2H
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes:
260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



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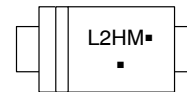
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**SCHOTTKY BARRIER
RECTIFIER
2.0 AMPERES
100 VOLTS**



**SOD-123FL
CASE 498
PLASTIC**

MARKING DIAGRAM



L2H = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBR2H100SFT3G	SOD-123 (Pb-Free)	10000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MBR2H100SFT3G

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current ($T_L = 146^\circ\text{C}$)	I_O	2.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	50	A
Storage and Operating Junction Temperature Range (Note 1)	T_{stg}, T_J	-65 to +175	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	23	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	85	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	330	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) ($I_F = 1.0 \text{ A}, T_J = 25^\circ\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 25^\circ\text{C}$) ($I_F = 1.0 \text{ A}, T_J = 125^\circ\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 125^\circ\text{C}$)	V_F	0.76 0.84 0.61 0.68	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	40 0.5	μA mA

- Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
- Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board.
- Pulse Test: Pulse Width $\leq 380 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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TYPICAL CHARACTERISTICS

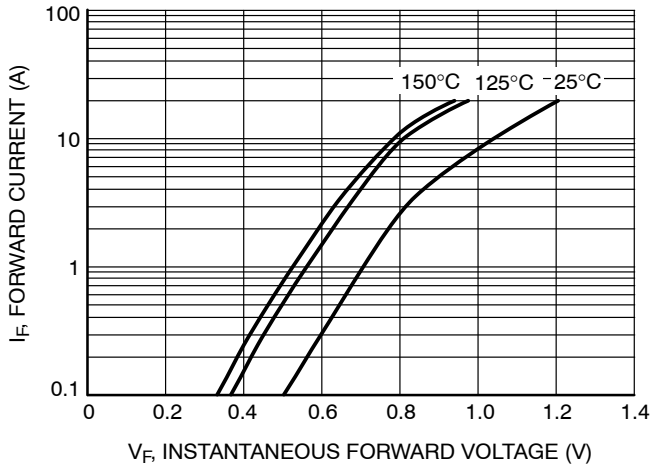


Figure 1. Typical Forward Voltage

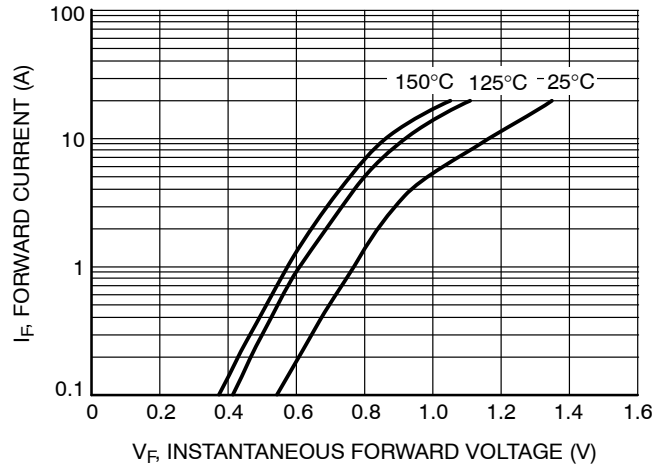


Figure 2. Maximum Forward Voltage

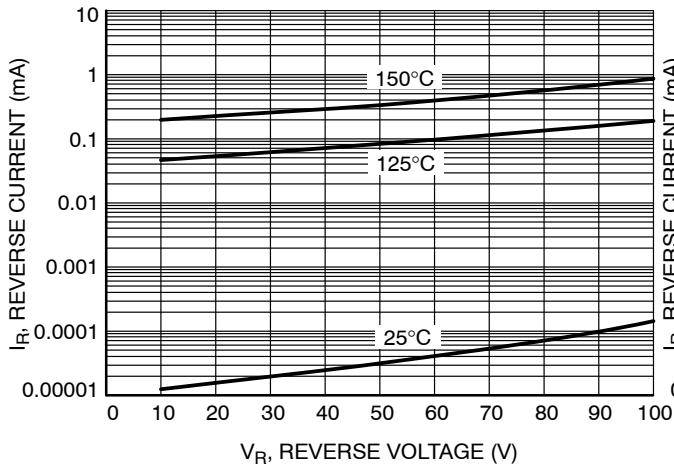


Figure 3. Typical Reverse Current

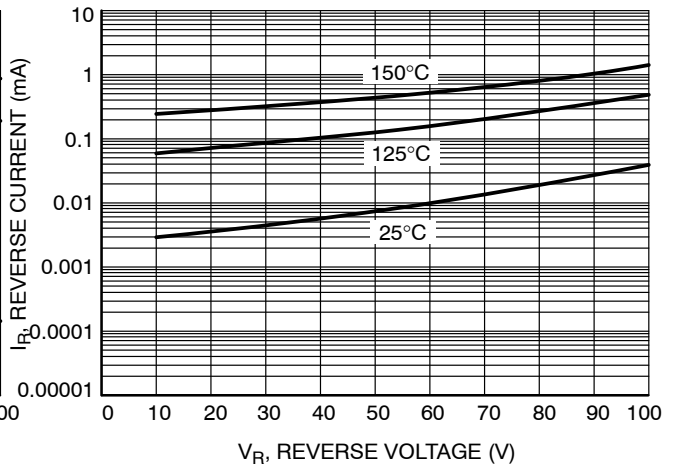


Figure 4. Maximum Reverse Current

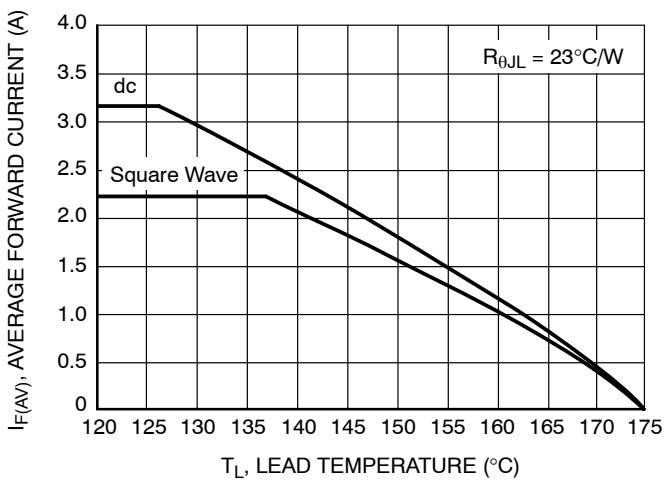


Figure 5. Current Derating

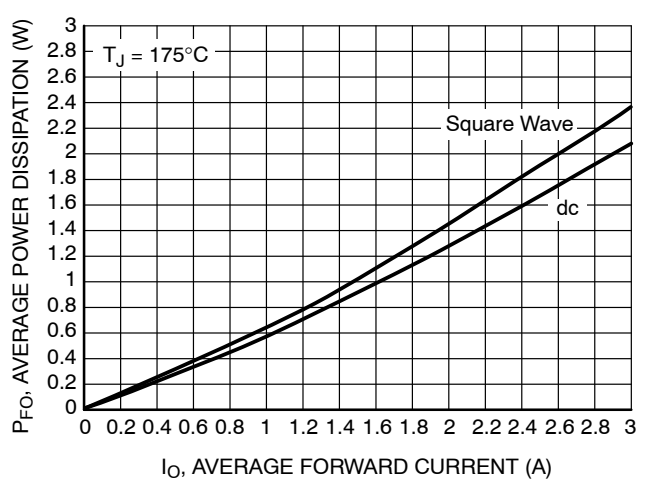


Figure 6. Forward Power Dissipation

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TYPICAL CHARACTERISTICS

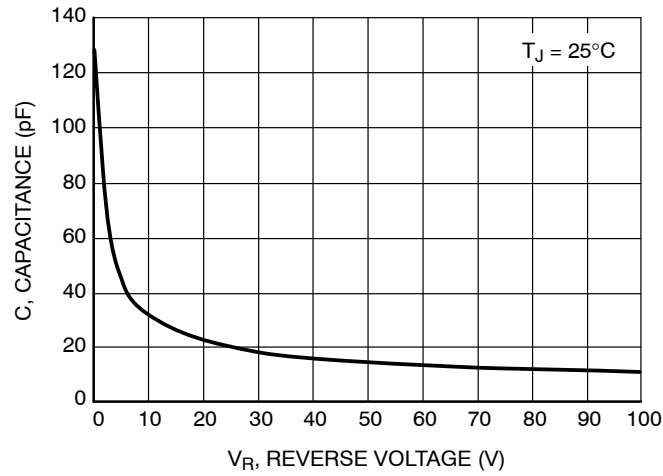


Figure 7. Capacitance

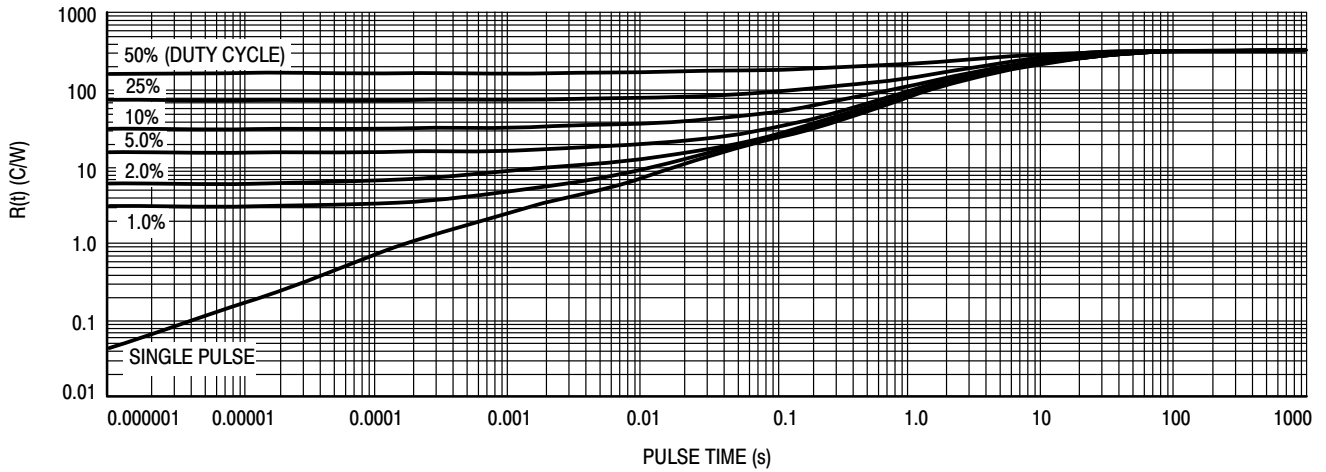


Figure 8. Thermal Response, Junction-to-Ambient (20 mm² pad)

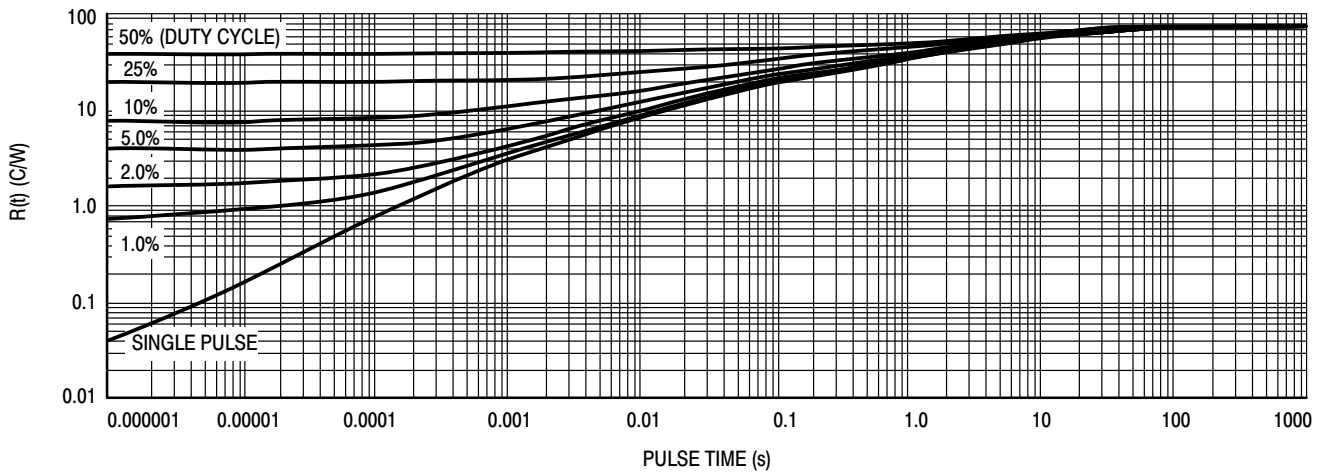
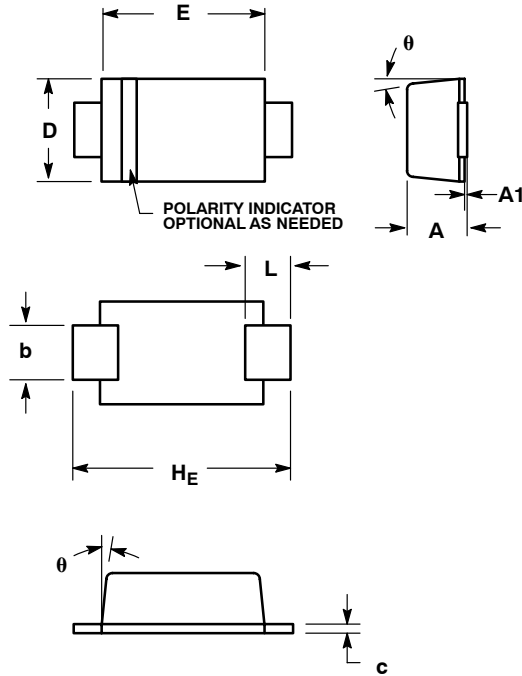


Figure 9. Thermal Response, Junction-to-Ambient (1 in² pad)

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PACKAGE DIMENSIONS

SOD-123LF
CASE 498-01
ISSUE A

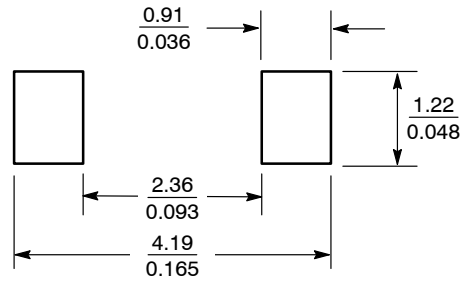


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH.
4. DIMENSIONS D AND J ARE TO BE MEASURED ON FLAT SECTION OF THE LEAD: BETWEEN 0.10 AND 0.25 MM FROM THE LEAD TIP.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	0.95	1.00	0.035	0.037	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.70	0.90	1.10	0.028	0.035	0.043
c	0.10	0.15	0.20	0.004	0.006	0.008
D	1.50	1.65	1.80	0.059	0.065	0.071
E	2.50	2.70	2.90	0.098	0.106	0.114
L	0.55	0.75	0.95	0.022	0.030	0.037
H _E	3.40	3.60	3.80	0.134	0.142	0.150
θ	0°	-	8°	0°	-	8°

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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